

N-Channel Power MOSFET

30V, 55A, 8mΩ

FEATURES

- Fast switching
- 100% EAS Guaranteed
- Green Device Available
- G-S ESD Protection Diode Embedded

APPLICATION

- Vcore / MB
- POL Application
- SMPS 2nd SR

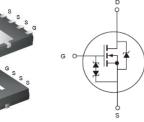
KEY PERFORMANCE PARAMETERS			
PARAMETER		VALUE	UNIT
V_{DS}		30	V
R _{DS(on)} (max)	$V_{GS} = 10V$	8	•
	$V_{GS} = 4.5V$	12.5	mΩ
Q_{g}		7.5	nC











Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	30	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current (Note 1)	$T_C = 25^{\circ}C$	l _D	55	Α	
Continuous Drain Current	T _C = 100°C		35		
Pulsed Drain Current (Note 2)		I _{DM}	220	А	
Total Power Dissipation @ T _C = 25°C		P_{DTOT}	54	W	
Single Pulsed Avalanche Energy (Note 3)		E_AS	45	mJ	
Single Pulsed Avalanche Current (Note 3)		I _{AS}	30	А	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	- 55 to +150	°C	

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Case Thermal Resistance	R _{eJC}	2.3	°C/W	
Junction to Ambient Thermal Resistance	$R_{\Theta JA}$	62	°C/W	

Notes: R_{eJA} is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. R_{eJA} is guaranteed by design while R_{eCA} is determined by the user's board design. R_{eJA} shown below for single device operation on FR-4 PCB in still air.



ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)		•				
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	30			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1	1.6	2.5	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±10	μA
Zero Gate Voltage Drain Current	$V_{DS} = 30V, V_{GS} = 0V$	I _{DSS}			1	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 16A$			6.5	8	mΩ
	$V_{GS} = 4.5V, I_D = 8A$	$R_{DS(on)}$		9.5	12.5	mΩ
Dynamic (Note 5)						
Total Gate Charge	$V_{DS} = 15V, I_{D} = 20A,$ $V_{GS} = 4.5V$	Q_g		7.5		
Gate-Source Charge		Q_gs		1.3		nC
Gate-Drain Charge		Q_{gd}		4.5		
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	C _{iss}		750		
Output Capacitance		C _{oss}		150		pF
Reverse Transfer Capacitance		C _{rss}		110		
Gate Resistance	F = 1MHz, open drain	R_g		2.7		Ω
Switching (Note 6)		•				
Turn-On Delay Time		t _{d(on)}		4.8		
Turn-On Rise Time	$V_{DD} = 15V,$ $R_{GEN} = 3.3\Omega,$ $I_{D} = 15A, V_{GS} = 10V,$	t _r		12.5		
Turn-Off Delay Time		t _{d(off)}		27.6		ns
Turn-Off Fall Time		t _f		8.2		
Source-Drain Diode (Note 4)						
Forward On Voltage	I _S = 1A, V _{GS} = 0V	V _{SD}			1	V

Notes:

- 1. Current limited by package
- 2. Pulse width limited by the maximum junction temperature
- 3. L=0.1mH, $I_{AS}=30A$, $V_{DD}=25V$, $R_G=25\Omega$, Starting $T_J=25^{\circ}C$
- 4. Pulse test: PW \leq 300 μ s, duty cycle \leq 2%
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.



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ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM080N03EPQ56 RLG	PDFN56	2,500pcs / 13" Reel

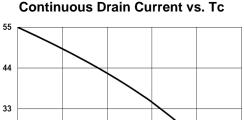
Note:

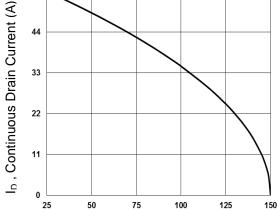
- 1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- 2. Halogen-free according to IEC 61249-2-21 definition



CHARACTERISTICS CURVES

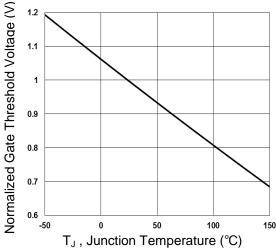
 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$



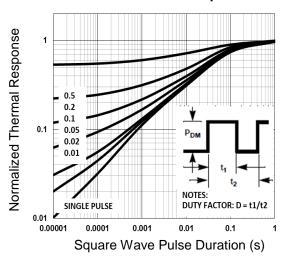




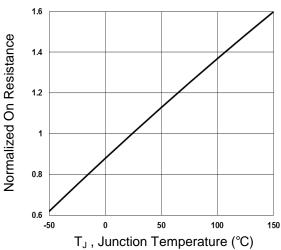
T_C, Case Temperature (°C)



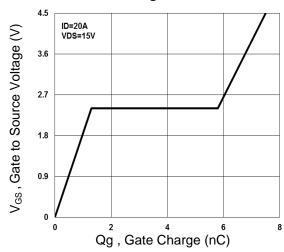
Normalized Transient Impedance



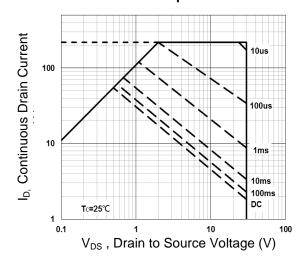
Normalized RDSON vs. T_J



Gate Charge Waveform

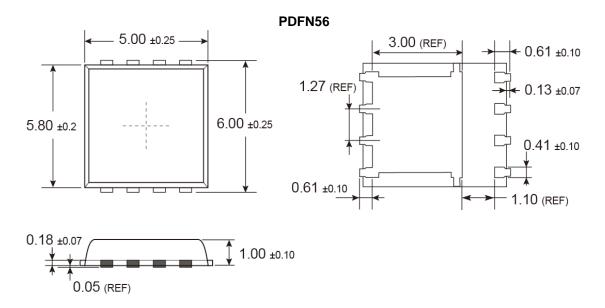


Maximum Safe Operation Area

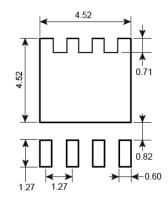




PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr S =May T =Jun U =Jul V =Aug

W = Sep X = Oct Y = Nov Z = Dec

 $L = \text{Lot Code } (1\sim9, A\sim Z)$



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